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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











ZXTN19060CFF

60V NPN HIGH GAIN POWER TRANSISTOR IN SOT23F

Features

- BV_{CEO} > 60V
- BV_{CEX} > 160V
- BV_{ECO} > 6V
- I_C = 5.5A Continuous Collector Current
- Low Saturation Voltage V_{CE(SAT)} < 45mV @ 1A
- $R_{CE(SAT)} = 26m\Omega$
- h_{FE} Characterised Up to 6A
- 1.5W Power Dissipation
- Complementary PNP Type: ZXTP19060CFF
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

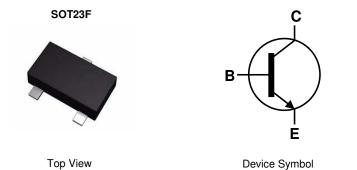
- Case: SOT23F
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208⁽³⁾
- Weight: 0.012 grams (Approximate)

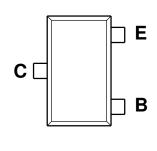
Description

Advanced process capability has been used to maximise the performance of this transistor. The SOT23F package is pin compatible with the industry standard SOT23 footprint but offers lower profile and higher dissipation for applications where power density is of utmost importance.

Applications

- Line Switching
- Motor Driving (Including DC Fans)
- High-Side Switches
- Subscriber Line Interface Cards (SLIC)





Top View

Pin Configuration

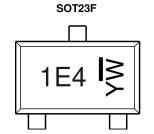
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTN19060CFFTA	AEC-Q101	1E4	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



1E4 = Product Type Marking Code YW = Date Code Marking Y = Year : 0~9

 \overline{W} = Week : A~Z : 1~26 a~z : 27~52

z represents 52 & 53 week



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	160	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEX}	160	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	6	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	5.5	Α
Peak Pulse Current	I _{CM}	12	Α
Base Current	I _B	1	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		0.84 6.72		
Power Dissipation	(Note 6)	D	1.34 10.72	W	
Linear Derating Factor	(Note 7)	P_{D}	1.50 12.0	mW/°C	
	(Note 8)		2.0 16.0		
	(Note 5)		149		
Thermal Decistores, Junction to Ambient	(Note 6)	Б	93	000	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	83	°C/W	
	(Note 8)		60		
Thermal Resistance, Junction to Lead (Note 9)		$R_{ heta JL}$	43.8	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

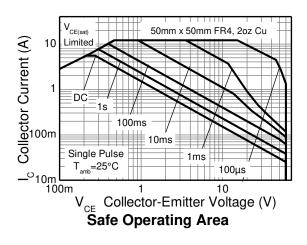
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	٧	С

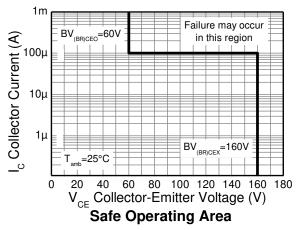
Notes:

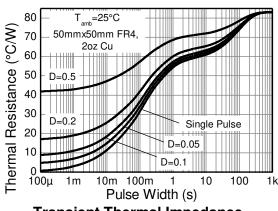
- 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
- 8. Same as Note 7, whilst measured at t < 5 seconds.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

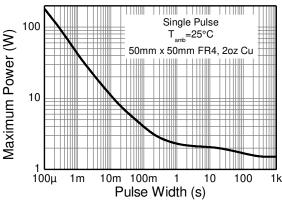


Thermal Characteristics and Derating Information



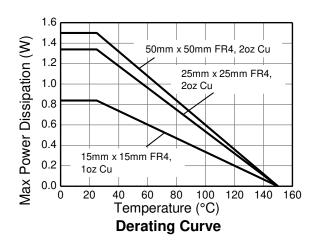






Transient Thermal Impedance

Pulse Power Dissipation





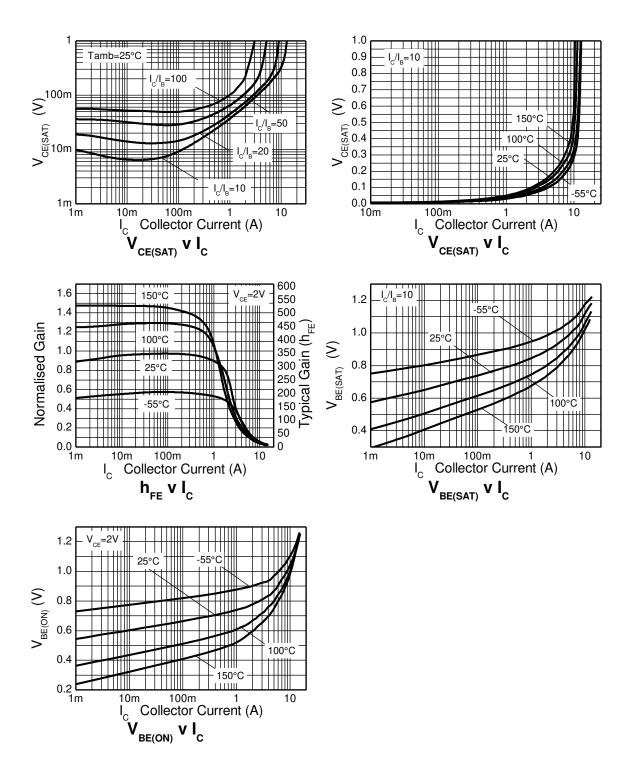
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	160	200	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Forward Blocking)	BV _{CEX}	160	200		V	I_C = 100 μ A, R_{BE} < 1 $k\Omega$ or -1 V < V_{BE} < 0.25 V
Collector-Emitter Breakdown Voltage (Base Open) (Note 11)	BV _{CEO}	60	75	1	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	_	V	I _E = 100μA
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV _{ECX}	6	7	_	V	I_E = 100μA, R_{BC} < 1k Ω or 0.25V < V_{BC} < -0.25V
Emitter-Collector Breakdown Voltage (Base Open)	BV _{ECO}	6	7	_	V	$I_E = 100\mu A$
Collector-Base Cutoff Current	Ісво	_	<1 —	50 0.5	nA μA	V _{CB} = 160V V _{CB} = 160V, T _A = +100°C
Emitter-Base Cutoff Current	I _{EBO}	_	<1	50	nA	V _{EB} = 5.6V
ON CHARACTERISTICS (Note 11)						
Static Forward Current Transfer Ratio	h _{FE}	200 160 30	350 280 50	500 — —	_	$I_C = 100$ mA, $V_{CE} = 2V$ $I_C = 2$ A, $V_{CE} = 2$ V $I_C = 6$ A, $V_{CE} = 2$ V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	36 105 105 145	45 150 135 175	mV	$I_{C} = 1A$, $I_{B} = 100mA$ $I_{C} = 1A$, $I_{B} = 10mA$ $I_{C} = 2A$, $I_{B} = 40mA$ $I_{C} = 5.5A$, $I_{B} = 550mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	1,000	1,100	mV	$I_C = 5.5A$, $I_B = 550mA$
Base-Emitter On Voltage	V _{BE(ON)}	_	880	1,000	mV	I _C =5.5A, V _{CE} = 2V
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	_	130	_	MHz	$I_C = 50 \text{mA}, V_{CE} = 10 \text{V},$ f = 50 MHz
Input Capacitance	C _{IBO}	_	310	_	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	Сово	_	19.3	25	pF	V _{CB} = 10V, f = 1MHz
Delay Time	t _D	_	27.3		ns	101/
Rise Time	t _R	_	13.2	_	ns	$V_{CC} = 10V$
Storage Time	ts	_	682	_	ns	$-I_{C} = 500 \text{mA},$ $-I_{B1} = I_{B2} = 50 \text{mA}$
Fall Time	t _F	_	90.9	_	ns	TIB1 = IB2 = SUITA

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

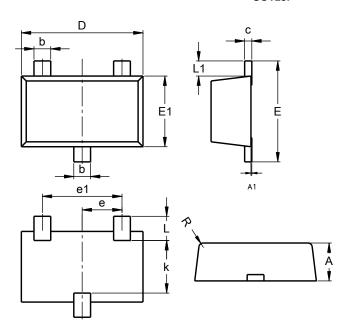




Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23F

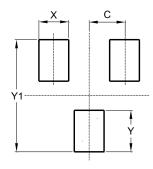


SOT23F					
Dim	Min Max Typ				
Α	0.80	1.00	0.90		
b	0.35	0.50	0.44		
C	0.10	0.20	0.16		
D	2.80	3.00	2.90		
е	0.95 REF				
e1	0.190 REF				
Е	2.30	2.50	2.40		
E1	1.50	1.70	1.65		
k	1.20	-	-		
L	0.30	0.65	0.50		
L1	0.30	0.50	0.40		
R	0.05	0.15	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23F



Dimensions	Value (in mm)		
C	0.95		
Х	0.80		
Υ	1.110		
Y1	3.000		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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